

Application No.: 10/082,318

Docket No.: 20402-00642-US

**AMENDMENTS TO THE SPECIFICATION**

Please amend the specification as follows:

Please replace the paragraph on page 7, lines 2-3, with the following amended paragraph:

The diaphragm may be made ~~form~~ from a compound of silicon and one of oxygen and nitrogen.

Please replace the paragraph starting on page 27, line 24 and continuing onto page 28, line 9 with the following amended paragraph:

A plurality of through holes 290 are, as shown in Fig. 3(f), formed in the bottom of the substrate 200 which extend vertically, as viewed in the drawing, into the sacrificial layer 140 through the first insulating layer 120, the first conductive layer 210, and the second insulating layer 330. The formation of each of the holes 290 is accomplished by removing the silicon of the substrate 200 using gases whose main component is sulfur hexafluoride (SF<sub>6</sub>) excited by plasma, after which the silicon oxide of the first insulating layer 120 is removed using chemical liquid such as hydrofluoric acid, the first conductive layer ~~210~~ is 210 is removed using a suitable etching liquid, and the silicon oxide of the second insulating layer 330 is removed using chemical liquid such as hydrofluoric acid.